

Page 29, replace the paragraph beginning at line 15, with the following rewritten paragraph:

96 --(d)- dielectric constant of 3.8 for 75% void and 25% silicon, from D.A.G. Bruggeman, Ann. Phys., Volume 24, page 636, 1935; and--.

IN THE CLAIMS

Please cancel without prejudice claims 1-23 and add newly written claims 24-31 as follows:

--24. (New) A method of fabricating an electroluminescent device including the steps of:

a) implanting a surface region of a silicon wafer, doped with a donor impurity to render the wafer n-type, with an acceptor impurity such that the surface region has a volume concentration of the acceptor impurity which is greater than a volume concentration of the donor impurity;

b) anodizing the wafer under illumination to produce a luminescent porous silicon region extending through the surface region; and

c) depositing an electrode on the porous silicon region;

wherein the condition (i) that at least a part of the region has an acceptor impurity volume concentration comparable with the solid solubility limit of the acceptor impurity in silicon is satisfied;

and/or wherein one or more of the following conditions are satisfied:

(ii) the surface region has a sheet resistivity greater than  $100 \Omega \text{ m}^{-1}$

immediately prior to the anodizing step;

- (iii) less than 1% of the acceptor impurity is electrically active prior to the anodizing step;
- (iv) the silicon wafer does not receive an anneal between steps (a) and (b);
- and
- (v) the anodization step (b) causes surface doping of silicon quantum wires within the porous silicon region, rendering the surface doped quantum wires p-type.

25. (New) A method of fabricating an electroluminescent device according to claim 24, wherein, when one or more of conditions (ii) to (v) apply, the anodization step (b) comprises the step of anodizing the wafer in aqueous hydrofluoric acid in such a manner that microporous porous silicon is formed.

26. (New) An electroluminescent device comprising a porous silicon region and electrical connections to the porous silicon region, wherein the porous silicon region contains a p-n junction therein.

27. (New) P-type porous silicon, wherein the porous silicon has a porosity greater than 30%.

28. (New) P-type porous silicon, according to claim 27 wherein the porous silicon comprises silicon quantum wires.

29. (New) P-type porous silicon according to claim 28 wherein the porous silicon has a porosity greater than 60%.

97 30. (New) Substantially wholly microporous visibly luminescent porous silicon, wherein the porous silicon is derived from n-type bulk silicon.

31. (New) An electroluminescent device comprising a porous silicon region and electrical connections to the porous silicon region, wherein the porous silicon region is a wholly microporous visibly luminescent region fabricated from n-type bulk silicon.--